## **SPTECH Silicon NPN Power Transistor**

2N6488

#### **DESCRIPTION**

- DC Current Gain Specified to 15 Amperes-
- : h<sub>FE</sub> =20-150@ I<sub>C</sub>= 5.0A =5.0(Min)@ I<sub>C</sub>=15A
- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>=80Vdc(Min)
- Complement to Type 2N6491

#### **APPLICATIONS**

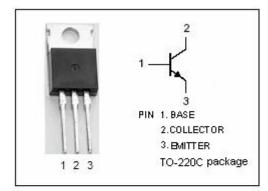
 Designed for use in general-purpose amplifier and switching applications

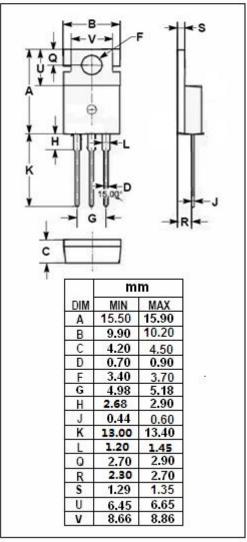
### ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
$V_{CBO}$	Collector-Base Voltage	90	V	
Vceo	Collector-Emitter Voltage	80	V	
V <sub>EBO</sub>	Emitter-Base Voltage 5		V	
Ic	Collector Current-Continuous	15	А	
lΒ	Base Current 5		А	
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C	75	W	
	Collector Power Dissipation @ T <sub>a</sub> =25 °C	1.8		
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$	

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.67	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	70	°C/W





1

# **SPTECH Silicon NPN Power Transistor**

2N6488

### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> =50mA ;I <sub>B</sub> =0	80		V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =5A; I <sub>B</sub> =0.5A		1.3	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =15A; I <sub>B</sub> =5.0A		3.5	V
V <sub>BE(on)-1</sub>	Base-Emitter On Voltage	I <sub>C</sub> =5A; V <sub>CE</sub> =4V		1.3	V
V <sub>BE(on)-2</sub>	Base-Emitter On Voltage	I <sub>C</sub> =15A ; V <sub>CE</sub> =4V		3.5	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> =40V;I <sub>B</sub> =0		1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> =5V; I <sub>C</sub> =0		1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> =5A; V <sub>CE</sub> =4V	20	150	
h <sub>FE-2</sub>	DC Current Gain	Ic=15A ; V <sub>CE</sub> =4V	5		
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> =1.0A; V <sub>CE</sub> =4V,f <sub>test</sub> =1.0MHz	5.0		MHz

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by SPTECH manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B